

3DG181, 3DG182



NPN Silicon High Reverse Voltage High Frequency Middle Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications										Test Condition
			3DG181					3DG182					
			A	B	C	D	E	F	G	H	I	J	
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	60	100	140	180	220	60	100	140	180	220	I _c =0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	60	100	140	180	220	60	100	140	180	220	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 (I _E =0.1mA)					≥ 5 (I _E =0.1mA)					
Total Dissipation	P _{tot}	mW	700 (T _a =25°C)					700 (T _a =25°C)					
Max. Collector Current	I _{CM}	mA	200					300					
Junction Temperature	T _{jm}	°C	175										
Storage Temperature	T _{stg}	°C	-55~+175										
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.8 (I _c =100mA, I _B =10mA)					1.0 (I _c =200mA, I _B =20mA)					
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.0 (I _c =100mA, I _B =10mA)					1.2 (I _c =200mA, I _B =20mA)					
C-B Leakage Current	I _{CBO}	uA	1.0(V _{CB} =30V)										
C-E Leakage Current	I _{CEO}	uA	2.0(V _{CE} =30V)										
E-B Leakage Current	I _{EBO}	uA	1.0(V _{EB} =1.5V)										
DC Current Gain	h _{FE}		25~180 (V _{CE} =10V, I _c =50mA)					25~180 (V _{CE} =2V, I _c =200mA)					
Transition frequency	f _T	MHz	A~E:50,F~J:100 (V _{CE} =10V, I _c =20mA, f=30MHz)										

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple
h _{FE}	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: